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**GENUS INTEGRATES BARRIER AND FILM DEPOSITION
INTO A SINGLE, COST-EFFECTIVE STEP****Genus *LYNX2* RInG™ for Rapid Integrated Gate**

SUNNYVALE, Calif., July 12, 1999 – Genus, Inc. (NASDAQ: GGNS), announced a new technology that integrates both tungsten barrier and film deposition into a single processing step. The *LYNX2* RInG (Rapid Integrated Gate) product is offered on the Genus *LYNX2*™ modular, single wafer platform currently in demonstration with multiple customers in an advanced R&D environment. The *LYNX2* RInG is a unique tungsten nitride film that provides a gate solution for 0.13-micron linewidths for 4Gbit DRAM production, extendable to 2012 (50 nm), according to the 1999 International Technology Roadmap for Semiconductors (ITRS).

Currently the deposition process requires physical vapor deposition (PVD) methods to place an initial barrier on the wafer, followed by chemical vapor deposition (CVD) to deposit a separate tungsten film layer. The *LYNX2* RInG eliminates this two-step process by converting the tungsten with a built in tungsten silicide barrier at the interface. The conversion is carried out rapidly and conveniently during the normal integration sequences of the deposition phase of wafer processing.

"The *LYNX2* RInG product is significant to Genus because the tungsten gate technology is extendable into DRAM production for quite some time to come," said Tom Seidel, chief technology officer of Genus. "Simplifying the deposition process by combining two steps is very attractive to DRAM manufacturers. This new technology can be easily integrated into current manufacturing operations and provides high level device performance, simplified integration and low cost-of-ownership."

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The *LYNX2* is an advanced, single wafer cluster tool. Proven in high-volume production, the *LYNX2* is a multiple film system with multiple-process module capability and a demonstrated high reliability in advanced manufacturing. It provides access to multiple films for the deposition of gate, capacitor and copper interconnect.

About Genus

Founded in 1982, Genus, Inc. designs, manufactures and markets capital equipment and deposition processes for advanced semiconductor manufacturing. The Company's thin film deposition products are used worldwide to produce integrated circuits for the data processing, communications, medical, military, transportation and consumer electronics industries. Genus' customers include semiconductor manufacturers located throughout the United States, Europe and the Pacific Rim including Korea, Japan and Taiwan. Genus' headquarters are located at 1139 Karlstad Drive, Sunnyvale, CA 94089, telephone (408) 747-7120; fax (408) 747-7199. For the most up-to-date company, product and financial information, visit Genus' web site at <http://www.genus.com>.

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